

General Description

The HSBB15P16D is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The HSBB15P16D meet the RoHS and Green Product requirement with full function reliability approved.

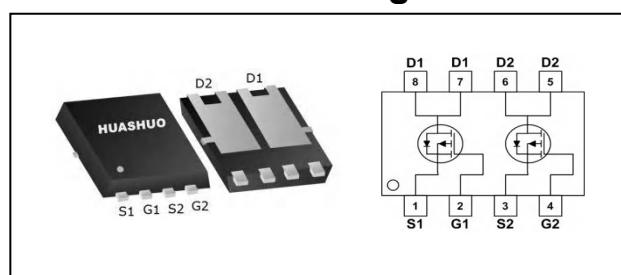
Product Summary

V_{DS}	-16	V
$R_{DS(ON),typ}$	12.5	m Ω
I_D	-15	A

Features

- Super Low Gate Charge
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

PRPAK3*3 Pin Configurations



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-16	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-15	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-12	A
I_{DM}	Pulsed Drain Current ²	-60	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ³	40	W
$P_D@T_C=70^{\circ}C$	Total Power Dissipation ³	32	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Case ¹	---	3.2	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-16	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V$, $I_D=-8A$	---	12.5	17	$m\Omega$
		$V_{GS}=-2.5V$, $I_D=-5A$	---	17.5	24	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-0.4	-0.7	-1.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-16V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	5.5	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-8V$, $V_{GS}=-4.5V$, $I_D=-7.5A$	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	1.7	---	
Q_{gd}	Gate-Drain Charge		---	5.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-8V$, $V_{GS}=-4.5V$, $R_G=3.3\Omega$, $I_D=-7.5A$	---	6	---	ns
T_r	Rise Time		---	38	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	52	---	
C_{iss}	Input Capacitance	$V_{DS}=-8V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1570	---	pF
C_{oss}	Output Capacitance		---	259	---	
C_{rss}	Reverse Transfer Capacitance		---	234	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-15	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-60	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

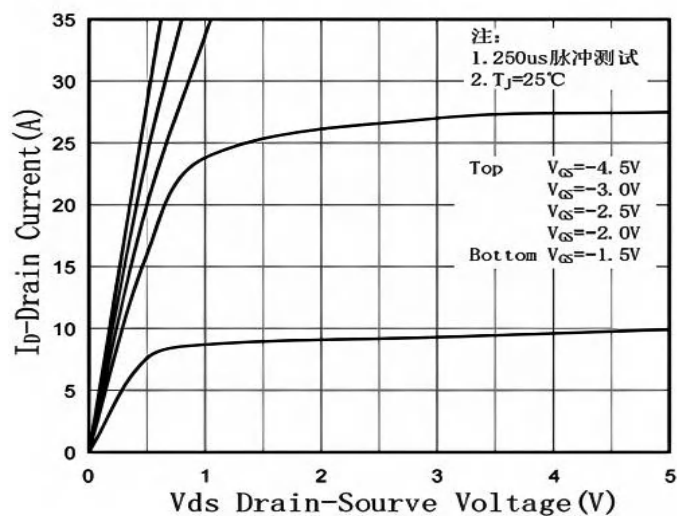


Fig.1 Output Characteristic

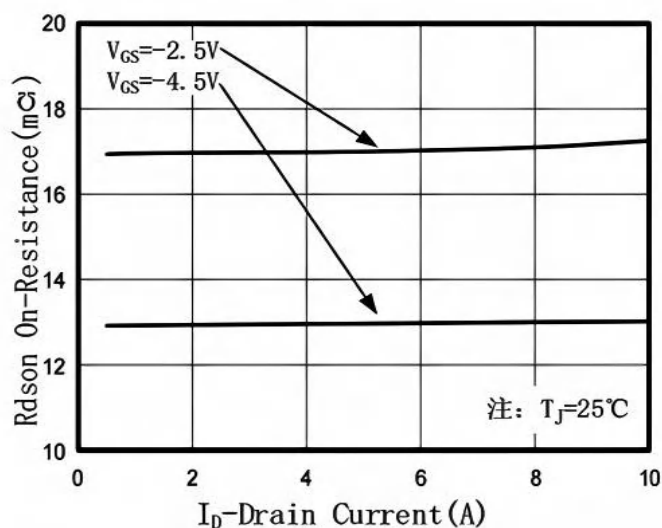


Fig.2 On-Resistance vs. Drain Current

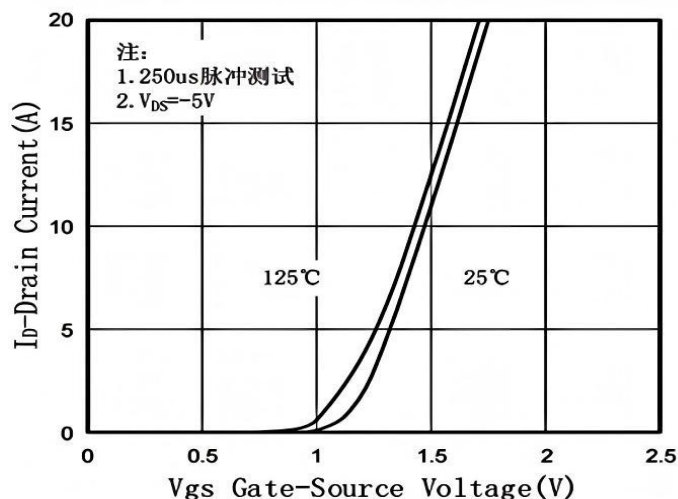


Fig.3 Transfer Characteristic

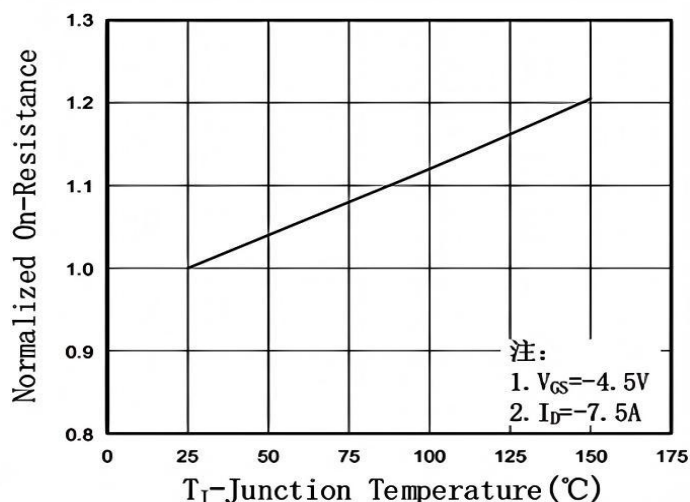


Fig.4 On-Resistance vs. Junction Temperature

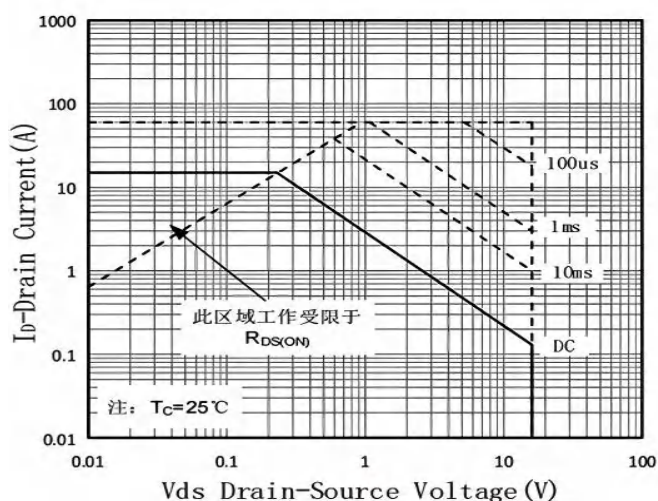


Fig.5 Safe Operation Area

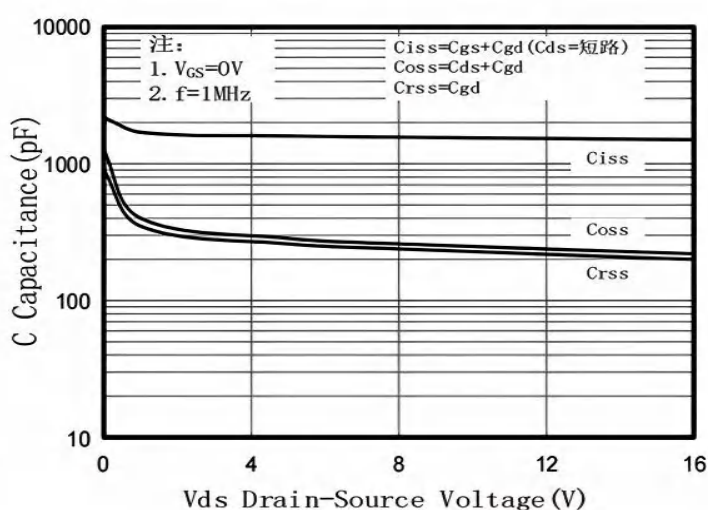


Fig.6 Capacitance Characteristic

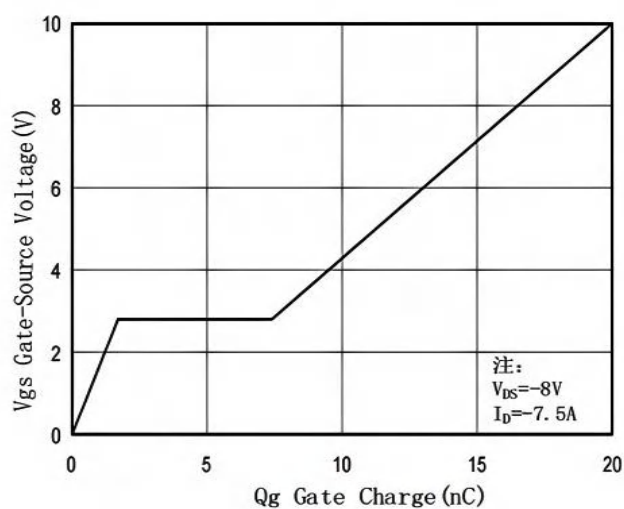


Fig.7 Gate-Charge Characteristic

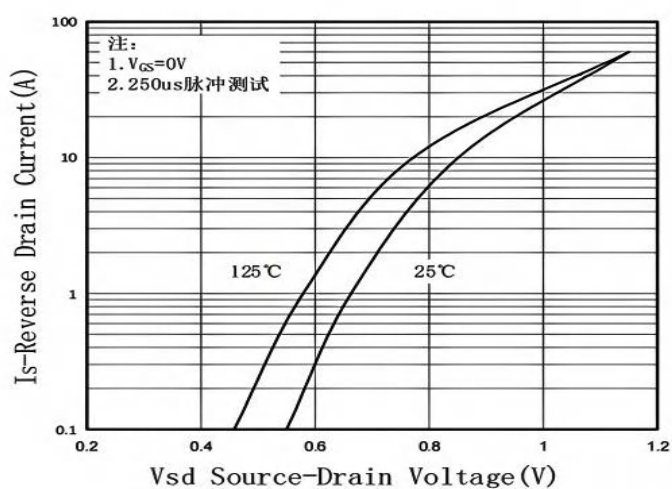


Fig.8 Body Diode Characteristic

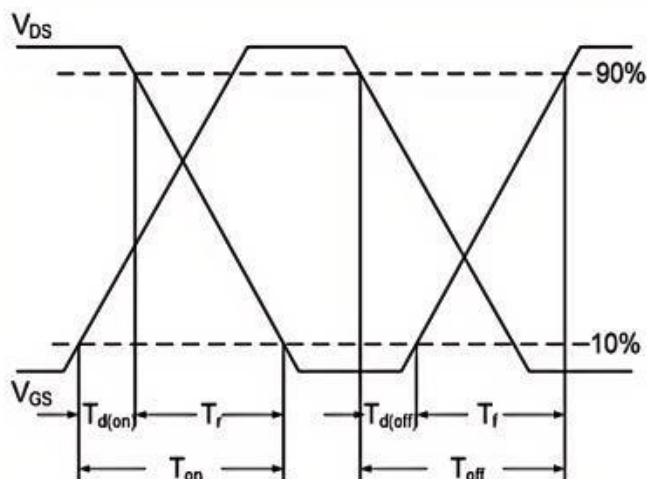


Fig.9 Switching Time Waveform

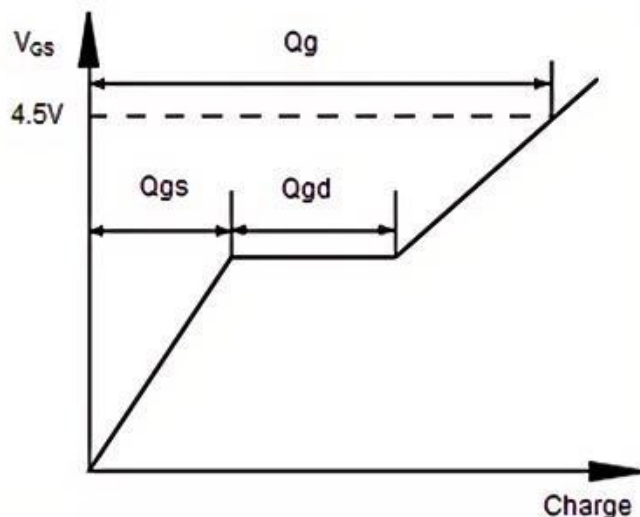
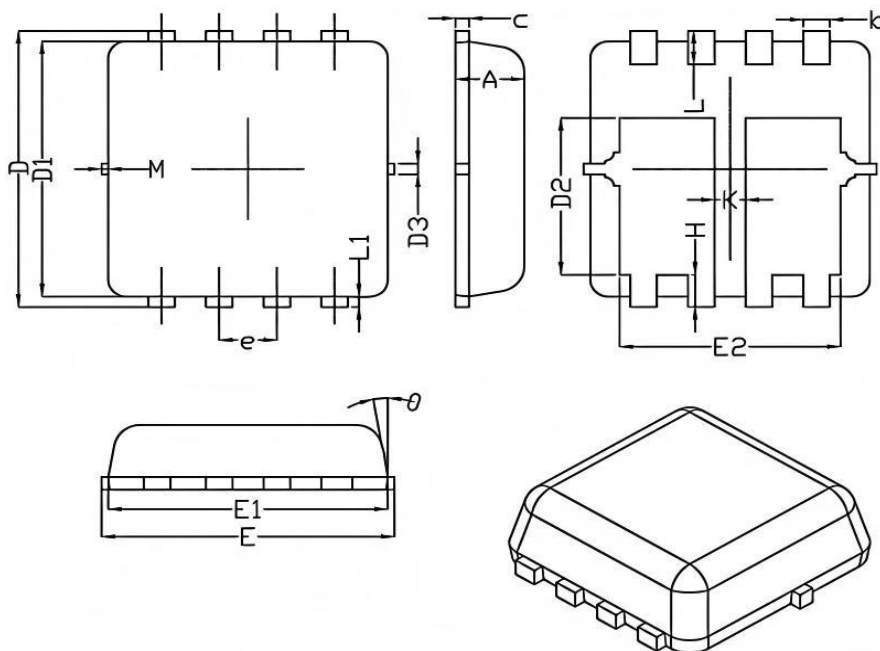


Fig.10 Gate Charge Waveform

Ordering Information

Part Number	Package code	Packaging
HSBB15P16D	PRPAK3*3	3000/Tape&Reel

PRPAK3*3 Dual Package Outline



SYMBOL	Dimensions In Millimeters		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
C	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
K	0.30	---	---
θ	---	10°	12°
M	*	*	0.15
*Not specified			

HSBB15P16D Marking:

